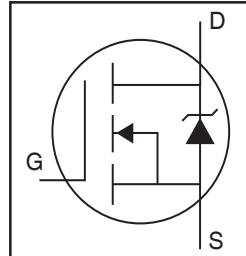
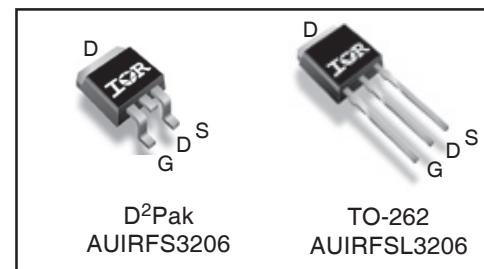


AUIRFS3206
AUIRFSL3206

HEXFET® Power MOSFET



V_{(BR)DSS}	60V
R_{DS(on)} typ.	2.4mΩ
max.	3.0mΩ
I_D (Silicon Limited)	210A ①
I_D (Package Limited)	120A



G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
I _D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	210①	A
I _D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	150 ①	
I _D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Package Limited)	120	
I _{DM}	Pulsed Drain Current ②	840	
P _D @ $T_C = 25^\circ\text{C}$	Maximum Power Dissipation	300	W
	Linear Derating Factor	2.0	W/°C
V _{GS}	Gate-to-Source Voltage	± 20	V
E _{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	170	mJ
I _{AR}	Avalanche Current ②	See Fig. 14, 15, 22a, 22b,	A
E _{AR}	Repetitive Avalanche Energy ②		mJ
dv/dt	Peak Diode Recovery ④	5.0	V/ns
T _J T _{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case ⑤	—	0.50	°C/W
R _{θJA}	Junction-to-Ambient (PCB Mount) , D ² Pak ⑤	—	40	

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

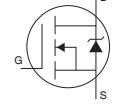
Static Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{\text{GS}} = 0\text{V}$, $I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.07	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 5\text{mA}$ ②
$R_{\text{DS}(\text{on})}$	Static Drain-to-Source On-Resistance	—	2.4	3.0	$\text{m}\Omega$	$V_{\text{GS}} = 10\text{V}$, $I_D = 75\text{A}$ ⑤
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{\text{DS}} = V_{\text{GS}}$, $I_D = 150\mu\text{A}$
g_{fs}	Forward Transconductance	210	—	—	S	$V_{\text{DS}} = 50\text{V}$, $I_D = 75\text{A}$
R_G	Internal Gate Resistance	—	0.7	—	Ω	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{\text{DS}} = 60\text{V}$, $V_{\text{GS}} = 0\text{V}$
		—	—	250		$V_{\text{DS}} = 48\text{V}$, $V_{\text{GS}} = 0\text{V}$, $T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{\text{GS}} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{\text{GS}} = -20\text{V}$

Dynamic Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise stated)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	—	120	170	nC	$I_D = 75\text{A}$
Q_{gs}	Gate-to-Source Charge	—	29	—		$V_{\text{DS}} = 30\text{V}$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	35	—		$V_{\text{GS}} = 10\text{V}$ ⑤
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{\text{gd}}$)	—	85	—		$I_D = 75\text{A}$, $V_{\text{DS}} = 0\text{V}$, $V_{\text{GS}} = 10\text{V}$
$t_{\text{d}(\text{on})}$	Turn-On Delay Time	—	19	—	ns	$V_{\text{DD}} = 30\text{V}$
t_r	Rise Time	—	82	—		$I_D = 75\text{A}$
$t_{\text{d}(\text{off})}$	Turn-Off Delay Time	—	55	—		$R_G = 2.7\Omega$
t_f	Fall Time	—	83	—		$V_{\text{GS}} = 10\text{V}$ ⑤
C_{iss}	Input Capacitance	—	6540	—	pF	$V_{\text{GS}} = 0\text{V}$
C_{oss}	Output Capacitance	—	720	—		$V_{\text{DS}} = 50\text{V}$
C_{rss}	Reverse Transfer Capacitance	—	360	—		$f = 1.0\text{MHz}$, See Fig.5
C_{oss} eff. (ER)	Effective Output Capacitance (Energy Related)	—	1040	—		$V_{\text{GS}} = 0\text{V}$, $V_{\text{DS}} = 0\text{V}$ to 48V ⑦, See Fig.11
C_{oss} eff. (TR)	Effective Output Capacitance (Time Related) ⑥	—	1230	—		$V_{\text{GS}} = 0\text{V}$, $V_{\text{DS}} = 0\text{V}$ to 48V ⑥

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_s	Continuous Source Current (Body Diode)	—	—	210①	A	MOSFET symbol showing the integral reverse p-n junction diode.
	Pulsed Source Current (Body Diode) ②	—	—	840		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}$, $I_s = 75\text{A}$, $V_{\text{GS}} = 0\text{V}$ ⑤
t_{rr}	Reverse Recovery Time	—	33	50	ns	$T_J = 25^\circ\text{C}$ $V_R = 51\text{V}$,
		—	37	56		$T_J = 125^\circ\text{C}$ $I_F = 75\text{A}$
Q_{rr}	Reverse Recovery Charge	—	41	62	nC	$T_J = 25^\circ\text{C}$ $\text{di}/\text{dt} = 100\text{A}/\mu\text{s}$ ⑤
		—	53	80		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	2.1	—	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 120A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.

② Repetitive rating; pulse width limited by max. junction temperature.

③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.023\text{mH}$ $R_G = 25\Omega$, $I_{\text{AS}} = 120\text{A}$, $V_{\text{GS}} = 10\text{V}$. Part not recommended for use above this value.

④ $I_{\text{SD}} \leq 75\text{A}$, $\text{di}/\text{dt} \leq 360\text{A}/\mu\text{s}$, $V_{\text{DD}} \leq V_{(\text{BR})\text{DSS}}$, $T_J \leq 175^\circ\text{C}$.

⑤ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.

⑥ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑦ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994. ⑨ R_θ is measured at T_J approximately 90°C

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level	3L-D2 PAK	MSL1	
	3L-TO-262	N/A	
ESD	Machine Model	Class M4(+/- 800V) ^{†††} (per AEC-Q101-002)	
	Human Body Model	Class H2(+/- 4000V) ^{†††} (per AEC-Q101-001)	
	Charged Device Model	Class C5(+/- 2000V) ^{†††} (per AEC-Q101-005)	
RoHS Compliant		Yes	

[†] Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

^{††} Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

^{†††} Highest passing voltage

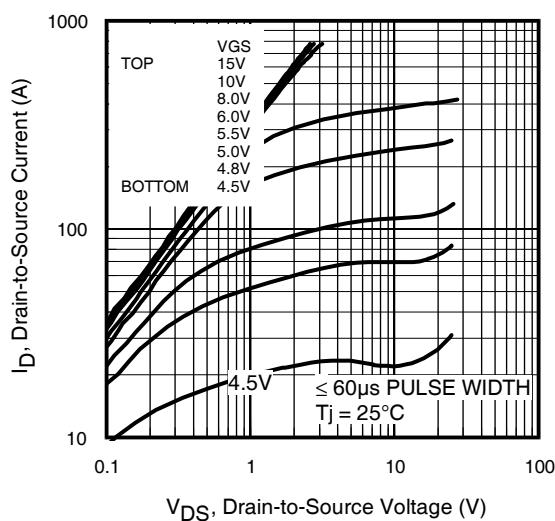


Fig 1. Typical Output Characteristics

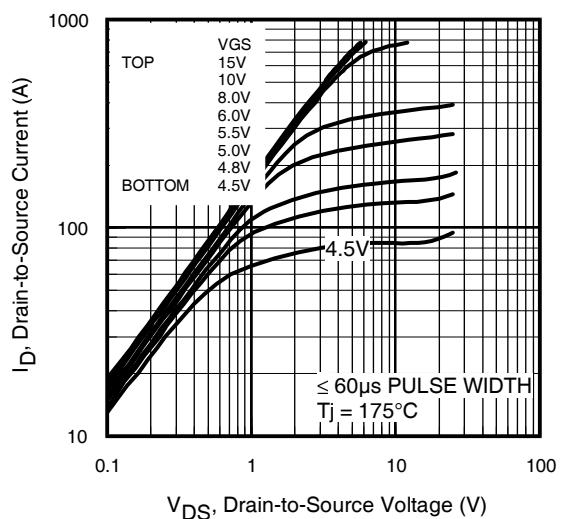


Fig 2. Typical Output Characteristics

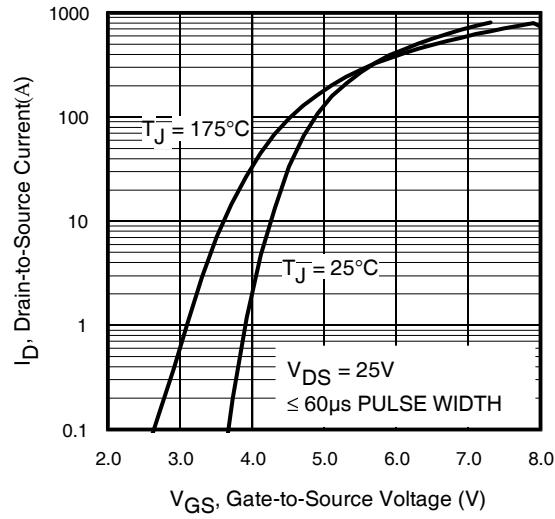


Fig 3. Typical Transfer Characteristics

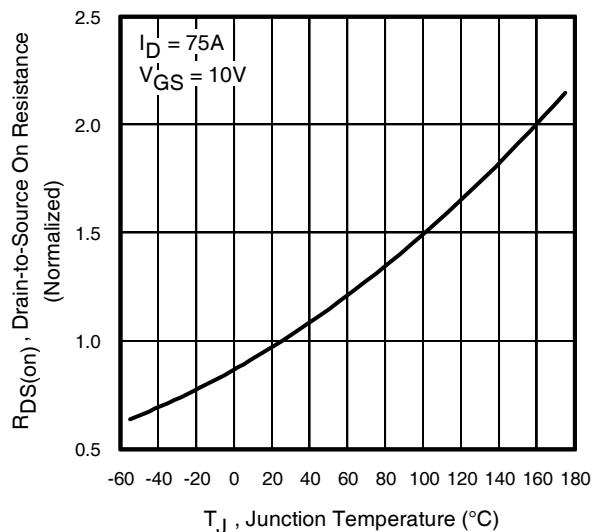


Fig 4. Normalized On-Resistance vs. Temperature

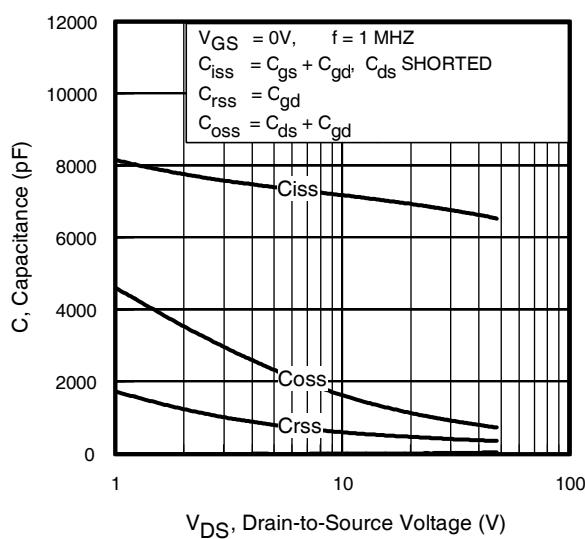


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

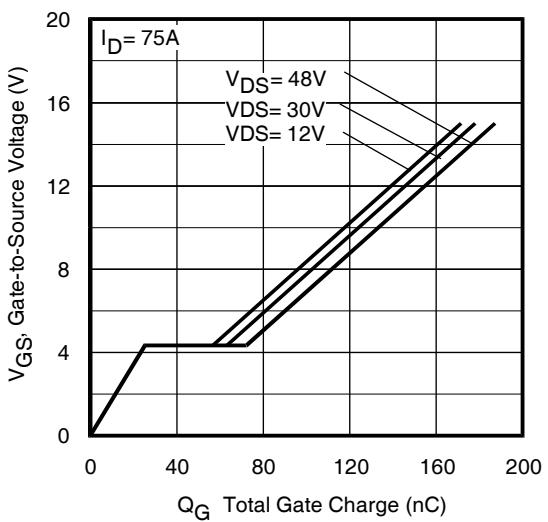


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

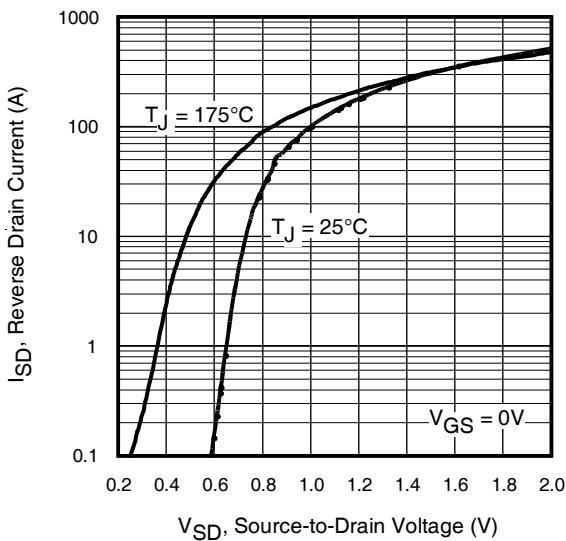


Fig 7. Typical Source-Drain Diode Forward Voltage

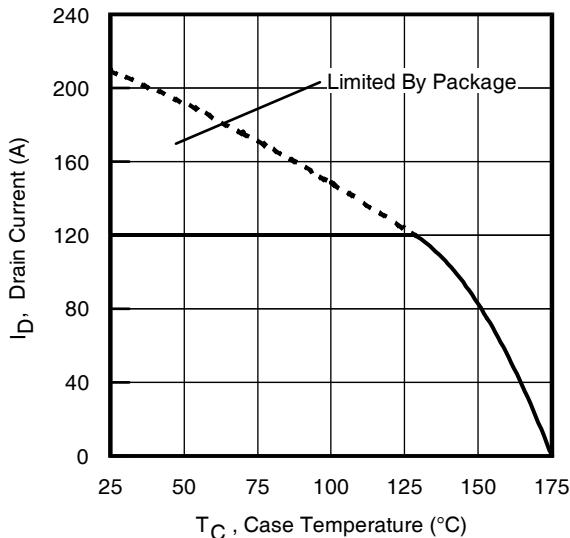


Fig 9. Maximum Drain Current vs. Case Temperature

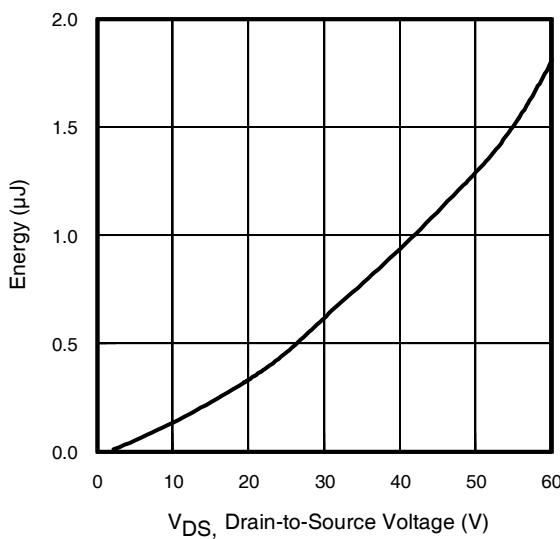


Fig 11. Typical C_{oss} Stored Energy

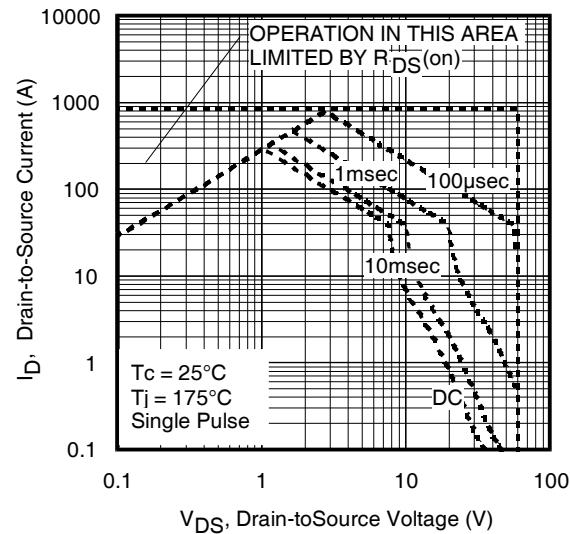


Fig 8. Maximum Safe Operating Area

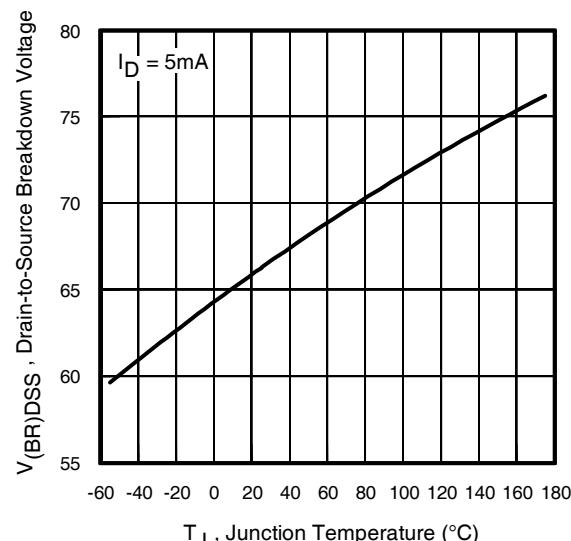


Fig 10. Drain-to-Source Breakdown Voltage

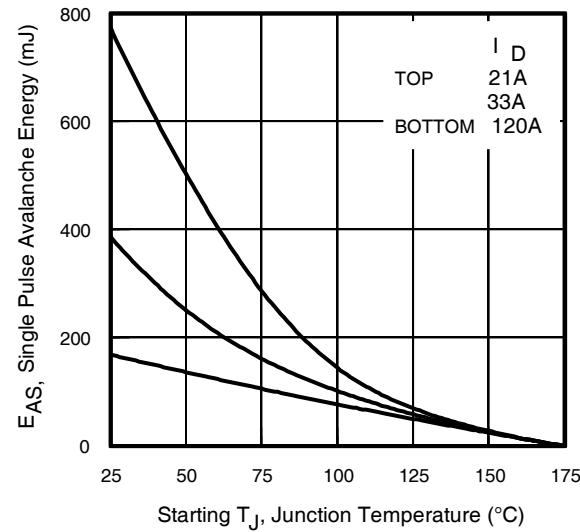


Fig 12. Maximum Avalanche Energy Vs. Drain Current

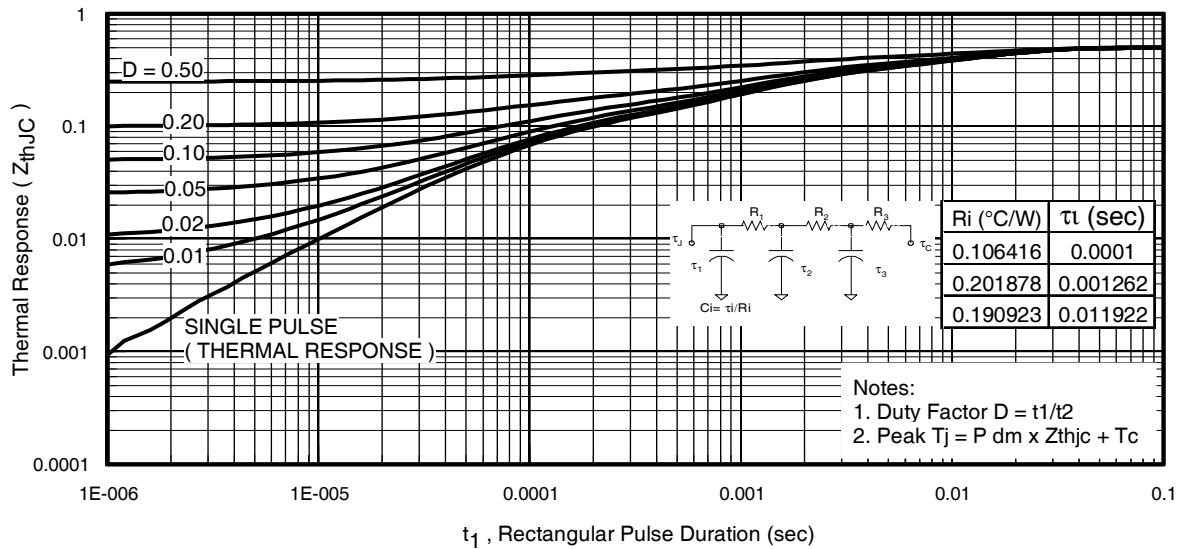


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

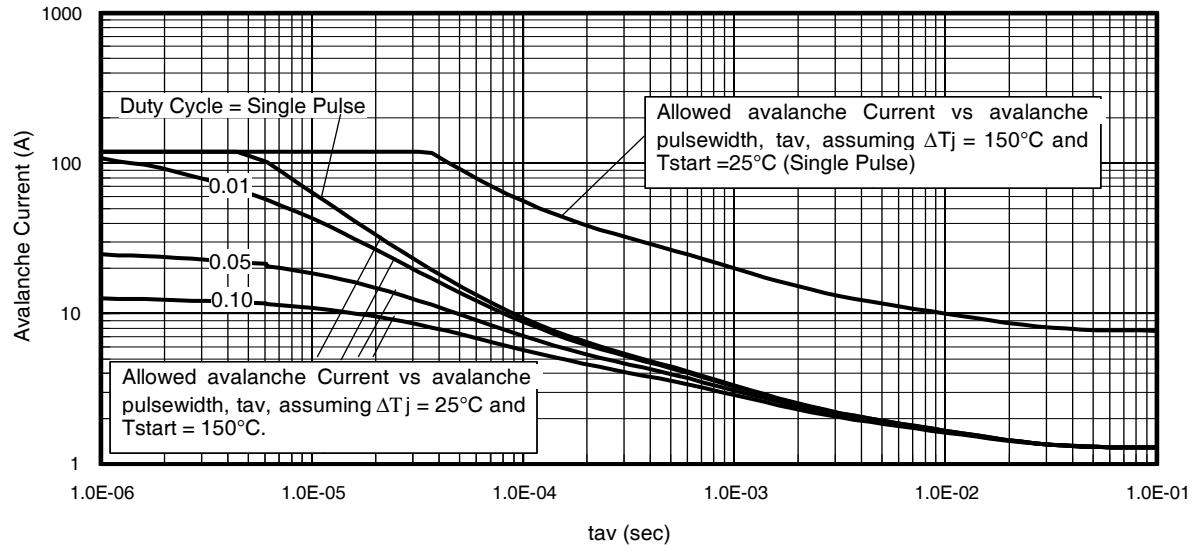
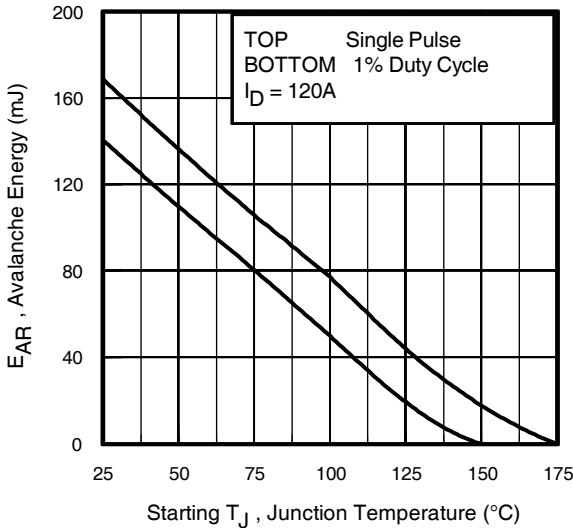


Fig 14. Typical Avalanche Current vs. Pulsewidth



Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as $25^{\circ}C$ in Figure 14, 15).

t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

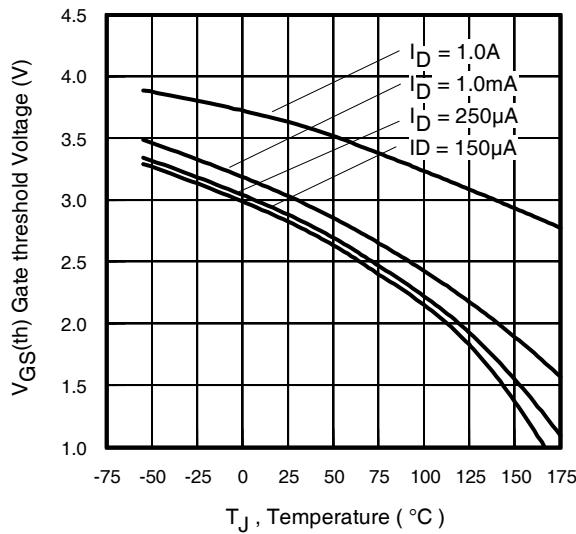


Fig. 16. Threshold Voltage Vs. Temperature

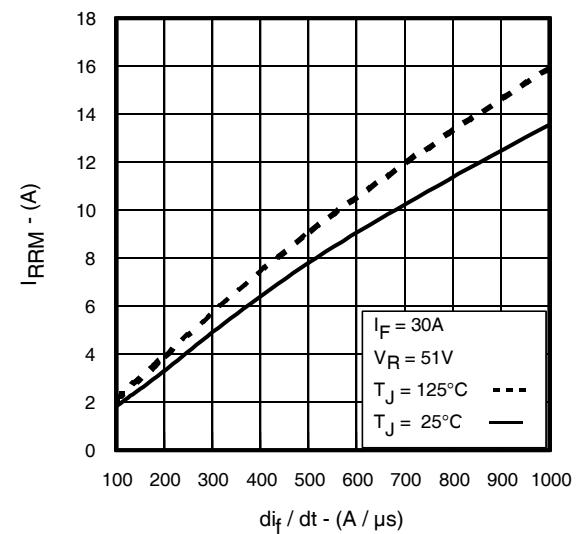


Fig. 17 - Typical Recovery Current vs. di_f/dt

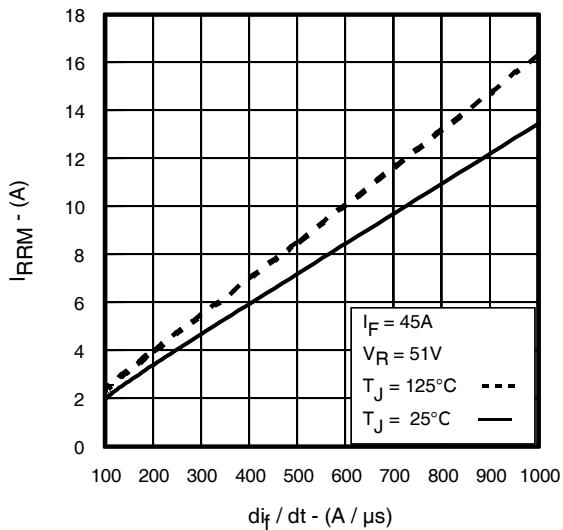


Fig. 18 - Typical Recovery Current vs. di_f/dt

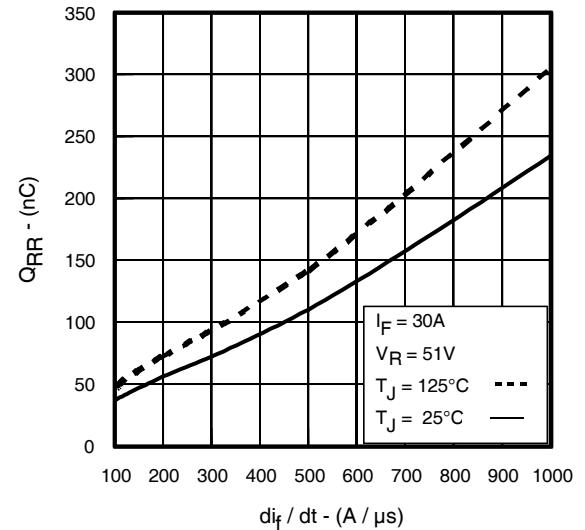


Fig. 19 - Typical Stored Charge vs. di_f/dt

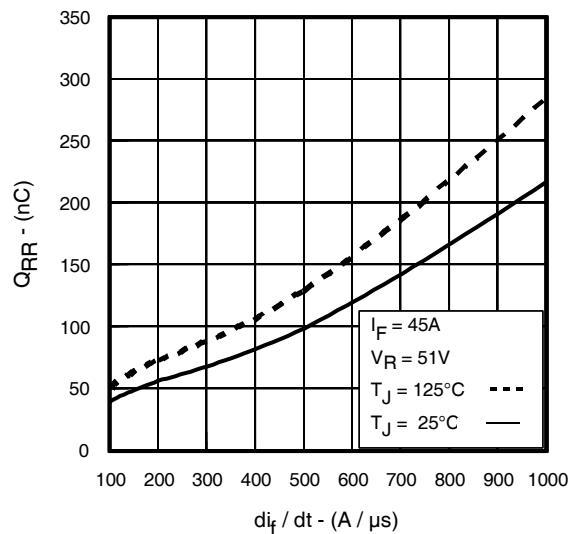


Fig. 20 - Typical Stored Charge vs. di_f/dt

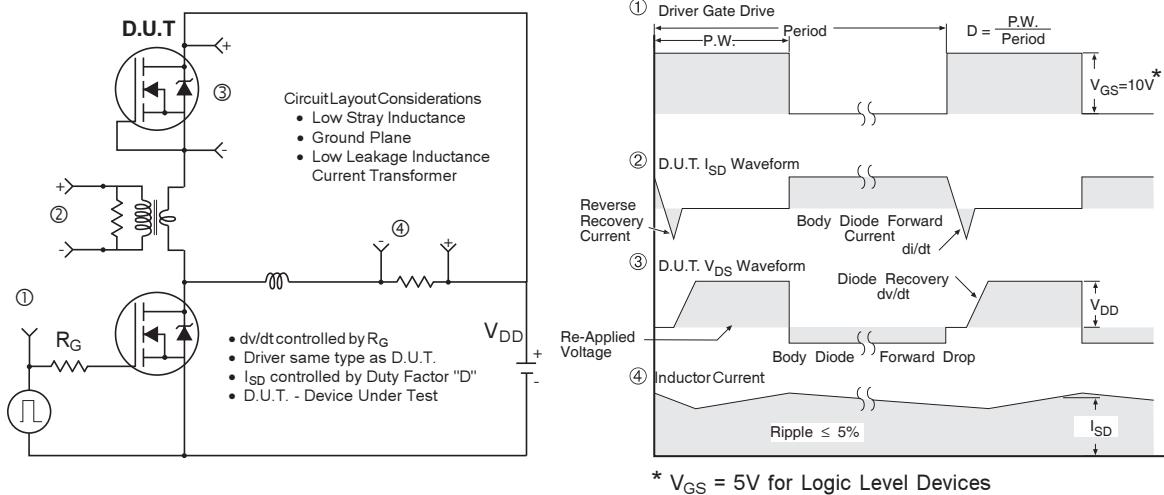


Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

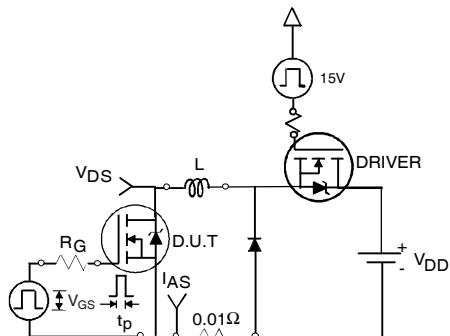


Fig 22a. Unclamped Inductive Test Circuit

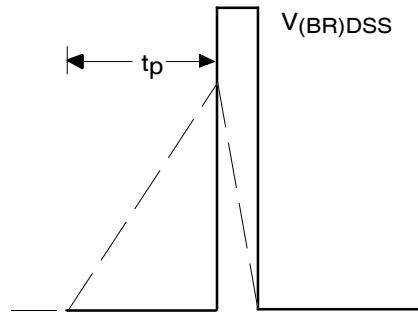


Fig 22b. Unclamped Inductive Waveforms

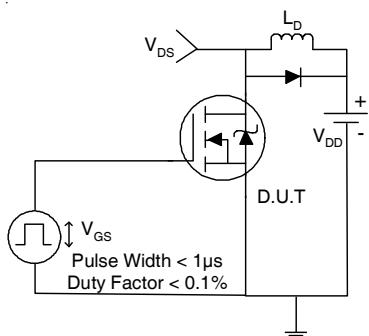


Fig 23a. Switching Time Test Circuit

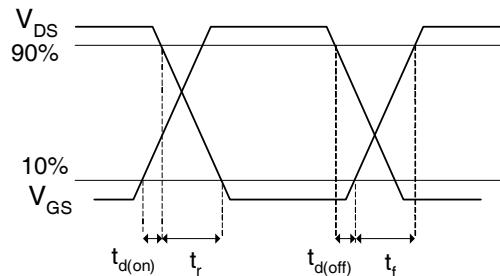


Fig 23b. Switching Time Waveforms

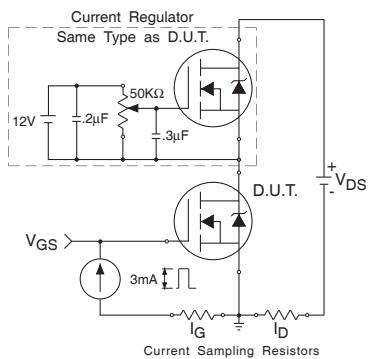


Fig 24a. Gate Charge Test Circuit

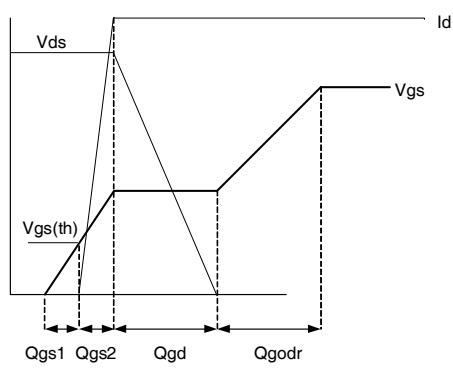
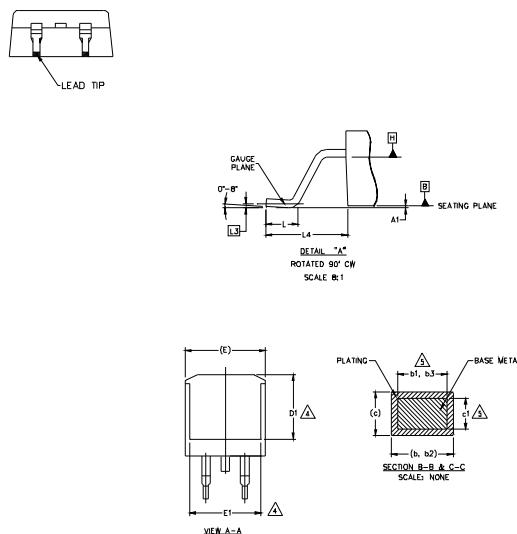
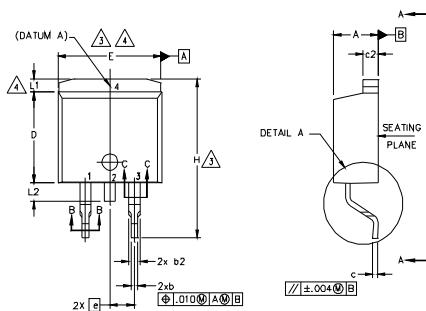


Fig 24b. Gate Charge Waveform

D²Pak Package Outline (Dimensions are shown in millimeters (inches))



NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
 3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
 4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
 5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
 6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
 7. CONTROLLING DIMENSION: INCH.
 8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

S Y M O L	DIMENSIONS			N O T E S	
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	5
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	5
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	5
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270		4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245		4
e	2.54	BSC	.100	BSC	
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.65	—	.066	
L2	1.27	1.78	—	.070	
L3	0.25	BSC	.010	BSC	
L4	4.78	5.28	.188	.208	

LEAD ASSIGNMENTS

HEXFET

1. GATE
2, 4. DRAIN
3. SOURCE

IGBTs, CoPACK

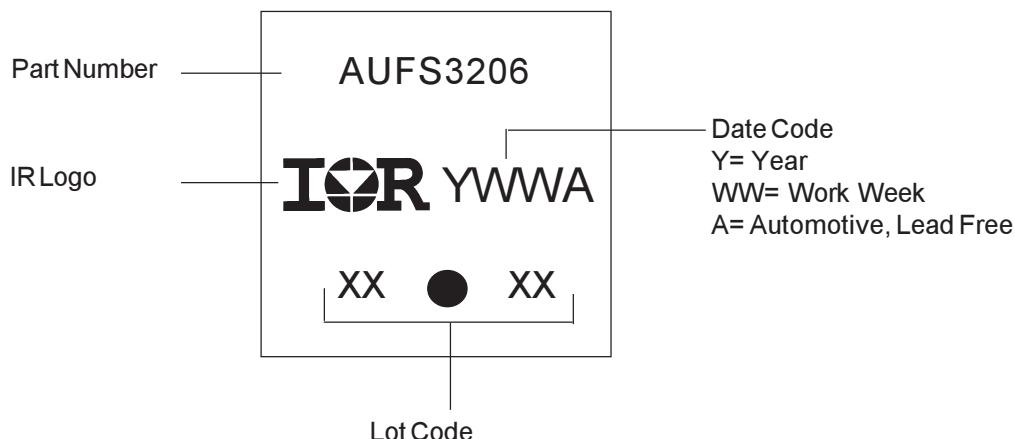
1. GATE
2, 4. COLLECTOR
3. Emitter

DIODES

1. ANODE *
2, 4. CATHODE
3. ANODE

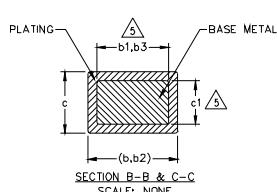
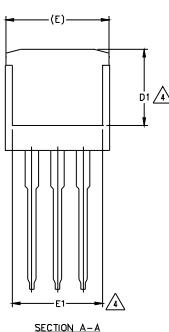
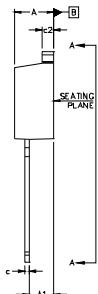
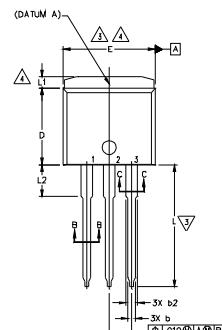
* PART DEPENDENT.

D²Pak Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

TO-262 Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. CONTROLLING DIMENSION: INCH.
7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

S Y M B O L	DIMENSIONS				N O T E S	
	MILLIMETERS		INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	4.06	4.83	.160	.190		
A1	2.03	3.02	.080	.119		
b	0.51	0.99	.020	.039		
b1	0.51	0.89	.020	.035	5	
b2	1.14	1.78	.045	.070		
b3	1.14	1.73	.045	.068	5	
c	0.38	0.74	.015	.029		
c1	0.38	0.58	.015	.023	5	
c2	1.14	1.65	.045	.065		
D	8.38	9.65	.330	.380	3	
D1	6.86	—	.270	—	4	
E	9.65	10.67	.380	.420	3,4	
E1	6.22	—	.245	—	4	
e	2.54 BSC	—	.100 BSC	—		
L	13.46	14.10	.530	.555		
L1	—	1.65	—	.065	4	
L2	3.56	3.71	.140	.146		

LEAD ASSIGNMENTS

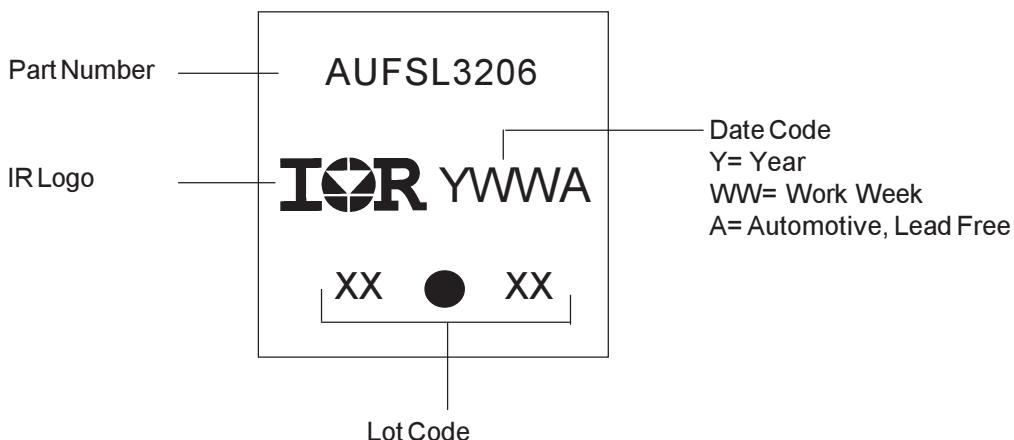
HEXFET

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

IGBTs, CoPACK

1. GATE
2. COLLECTOR
3. Emitter
4. COLLECTOR

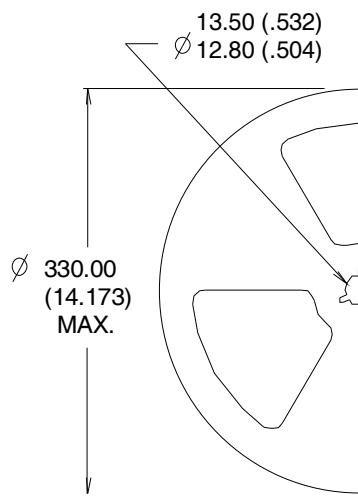
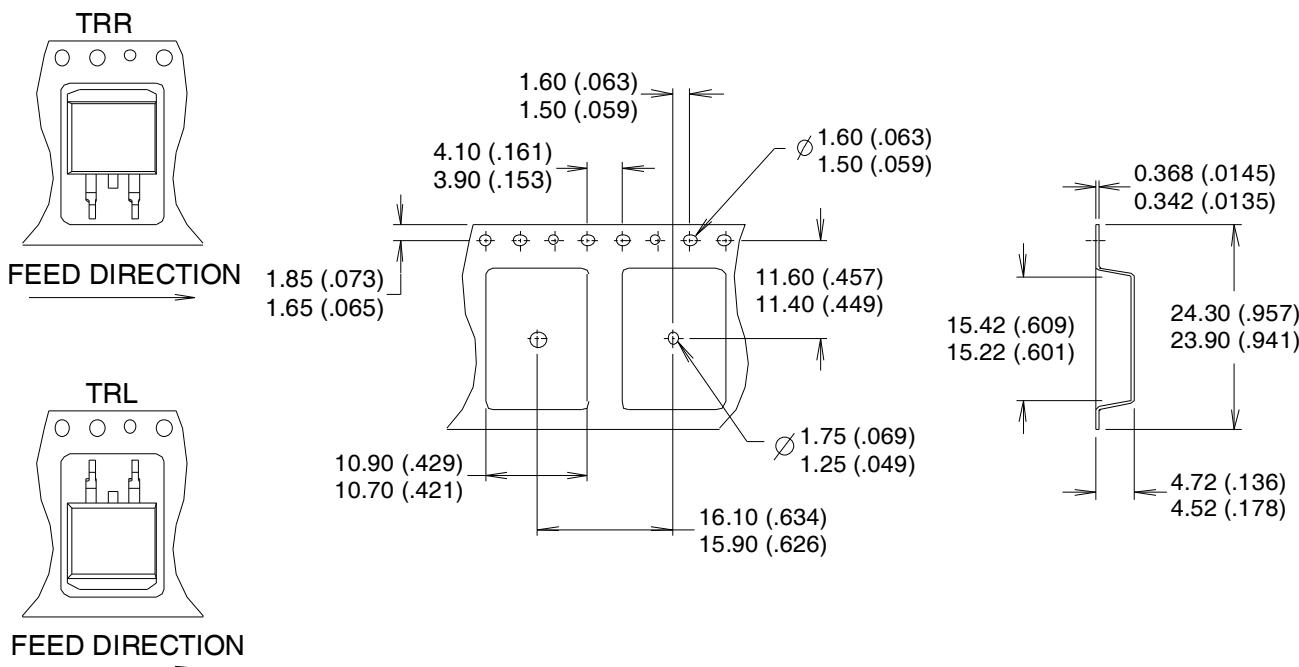
TO-262 Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

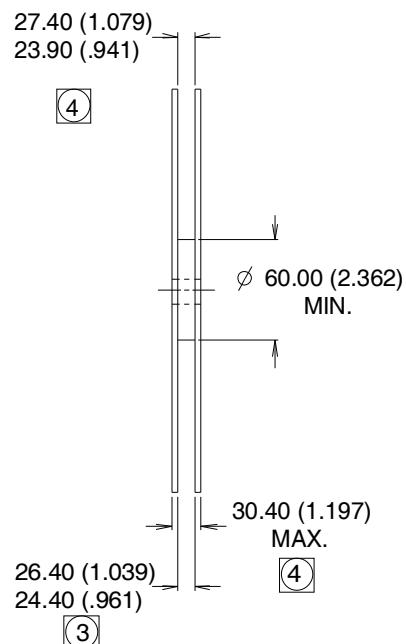
D²Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.



Ordering Information

Base part	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFSL3206	TO-262	Tube	50	AUIRFSL3206
AUIRFS3206	D2Pak	Tube	50	AUIRFS3206
		Tape and Reel Left	800	AUIRFS3206TRL
		Tape and Reel Right	800	AUIRFS3206TRR

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